

C6D10170H

6th Generation 1700 V, 10 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Types: TO-247-2
Marking: C6D10170H

Features

- Low Forward Voltage (V_f) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Low Profile Package with Low Inductance

Applications

- Industrial Switched Mode Power Supplies
- Uninterruptible & AUX Power Supplies
- Boost for PFC & DC-DC Stages
- Solar Inverters

Maximum Ratings ($T_c = 25^\circ\text{C}$ Unless Otherwise Specified)

| Parameter | Symbol | Value | Unit | Test Conditions | Notes |
|---|-------------|-------|----------------------|--|--------|
| Repetitive Peak Reverse Voltage | V_{RRM} | 1700 | V | | |
| DC Blocking Voltage | V_{DC} | 1700 | | | |
| Continuous Forward Current | I_F | 40 | A | $T_c = 25^\circ\text{C}$ | Fig. 3 |
| | | 21 | | $T_c = 125^\circ\text{C}$ | |
| | | 10 | | $T_c = 160^\circ\text{C}$ | |
| Repetitive Peak Forward Surge Current | I_{FRM} | 58 | A | $T_c = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$ | |
| | | 32 | | $T_c = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$ | |
| Non-Repetitive Peak Forward Surge Current | I_{FSM} | 148 | A | $T_c = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$ | Fig. 8 |
| | | 93 | | $T_c = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Wave}$ | |
| Power Dissipation | P_{tot} | 204 | W | $T_c = 25^\circ\text{C}$ | Fig. 4 |
| | | 88 | | $T_c = 110^\circ\text{C}$ | |
| i^2t Value | $\int i^2t$ | 109 | A^2s | $T_c = 25^\circ\text{C}, t_p = 10\text{ ms}$ | |
| | | 43 | | $T_c = 110^\circ\text{C}, t_p = 10\text{ ms}$ | |



Electrical Characteristics

| Parameter | Symbol | Typ. | Max. | Unit | Test Conditions | Notes |
|---------------------------|--------|------|------|---------------|--|--------|
| Forward Voltage | V_F | 1.45 | 1.7 | V | $I_F = 10 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$ | Fig. 1 |
| | | 2.0 | 2.8 | | $I_F = 10 \text{ A}, T_j = 175 \text{ }^\circ\text{C}$ | |
| Reverse Current | I_R | 4 | 18 | μA | $V_R = 1700 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$ | Fig. 2 |
| | | 24 | 90 | | $V_R = 1700 \text{ V}, T_j = 175 \text{ }^\circ\text{C}$ | |
| Total Capacitive Charge | Q_C | 126 | | nC | $V_R = 1700 \text{ V}, T_j = 25 \text{ }^\circ\text{C}$ | Fig. 5 |
| Total Capacitance | C | 1227 | | pF | $V_R = 0 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$ | Fig. 6 |
| | | 53 | | | $V_R = 800 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$ | |
| | | 52 | | | $V_R = 1700 \text{ V}, T_j = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$ | |
| Capacitance Stored Energy | E_C | 79 | | μJ | $V_R = 1700 \text{ V}$ | Fig. 7 |

Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

| Parameter | Symbol | Value | Unit | Notes |
|--|-------------------------------|-------------|-----------------------------|------------|
| Thermal Resistance, Junction to Case (Typical) | $R_{\theta, \text{JC (TYP)}}$ | 0.62 | $^\circ\text{C} / \text{W}$ | |
| Thermal Resistance, Junction to Case (Maximum) | $R_{\theta, \text{JC (MAX)}}$ | 0.73 | | |
| Junction Temperature | T_j | -55 to +175 | $^\circ\text{C}$ | |
| Case & Storage Temperature | T_c | -55 to +150 | | |
| TO-247 Mounting Torque | - | 1 | Nm | M3 Screw |
| | | 8.8 | lbf-in | 6-32 Screw |



Typical Performance

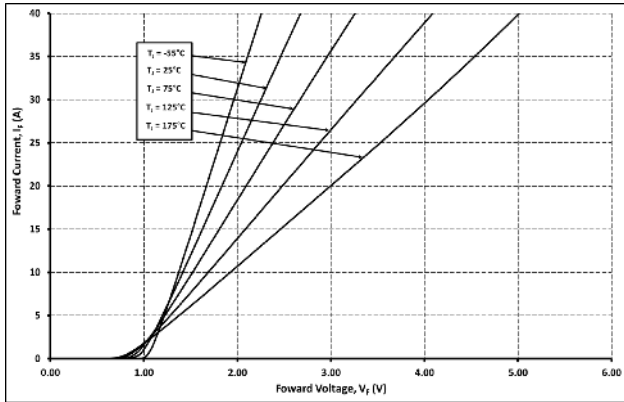


Figure 1
Forward Characteristics

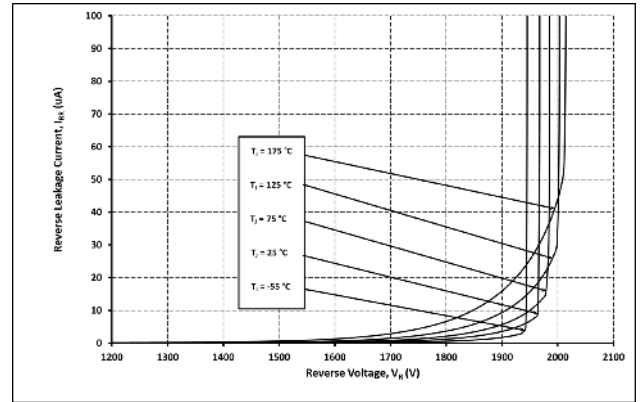


Figure 2
Reverse Characteristics

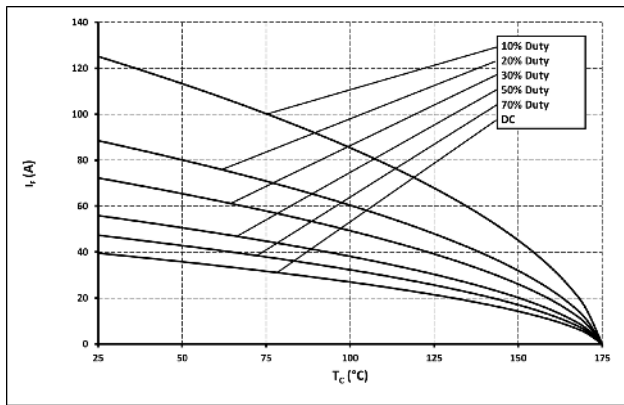


Figure 3
Current Derating

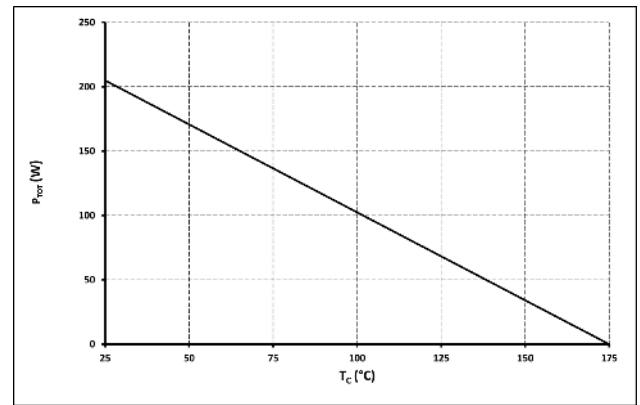


Figure 4
Power Derating

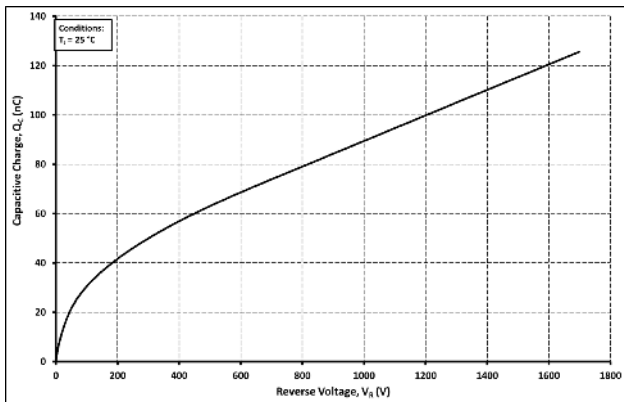


Figure 5
Total Capacitance Charge vs. Reverse Voltage

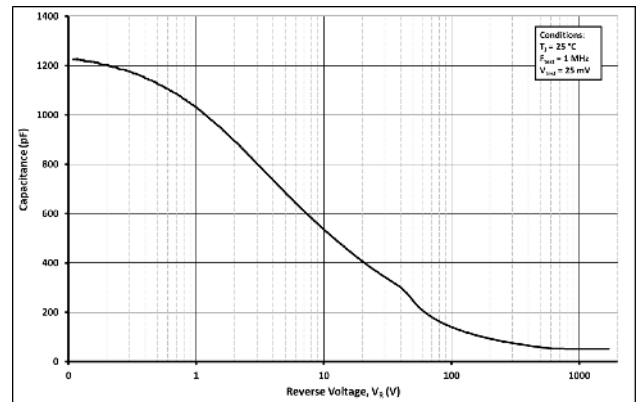


Figure 6
Capacitance vs. Reverse Voltage



Typical Performance

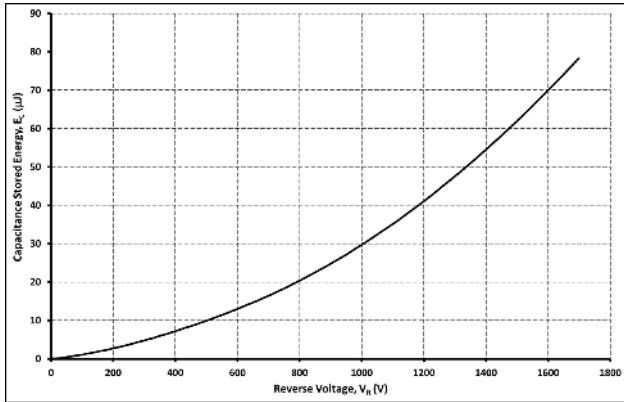


Figure 7
Capacitance Stored Energy

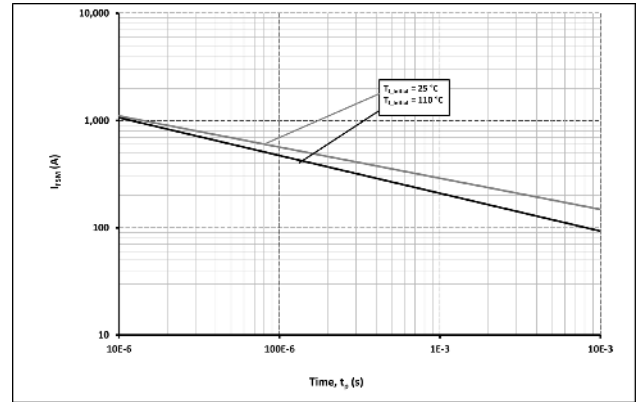


Figure 8
Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Sinusoidal Waveform)

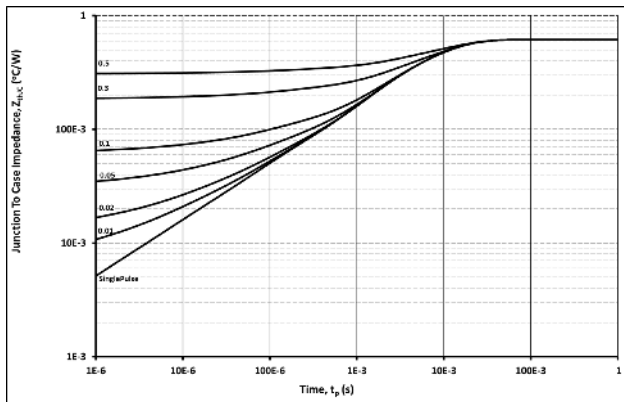
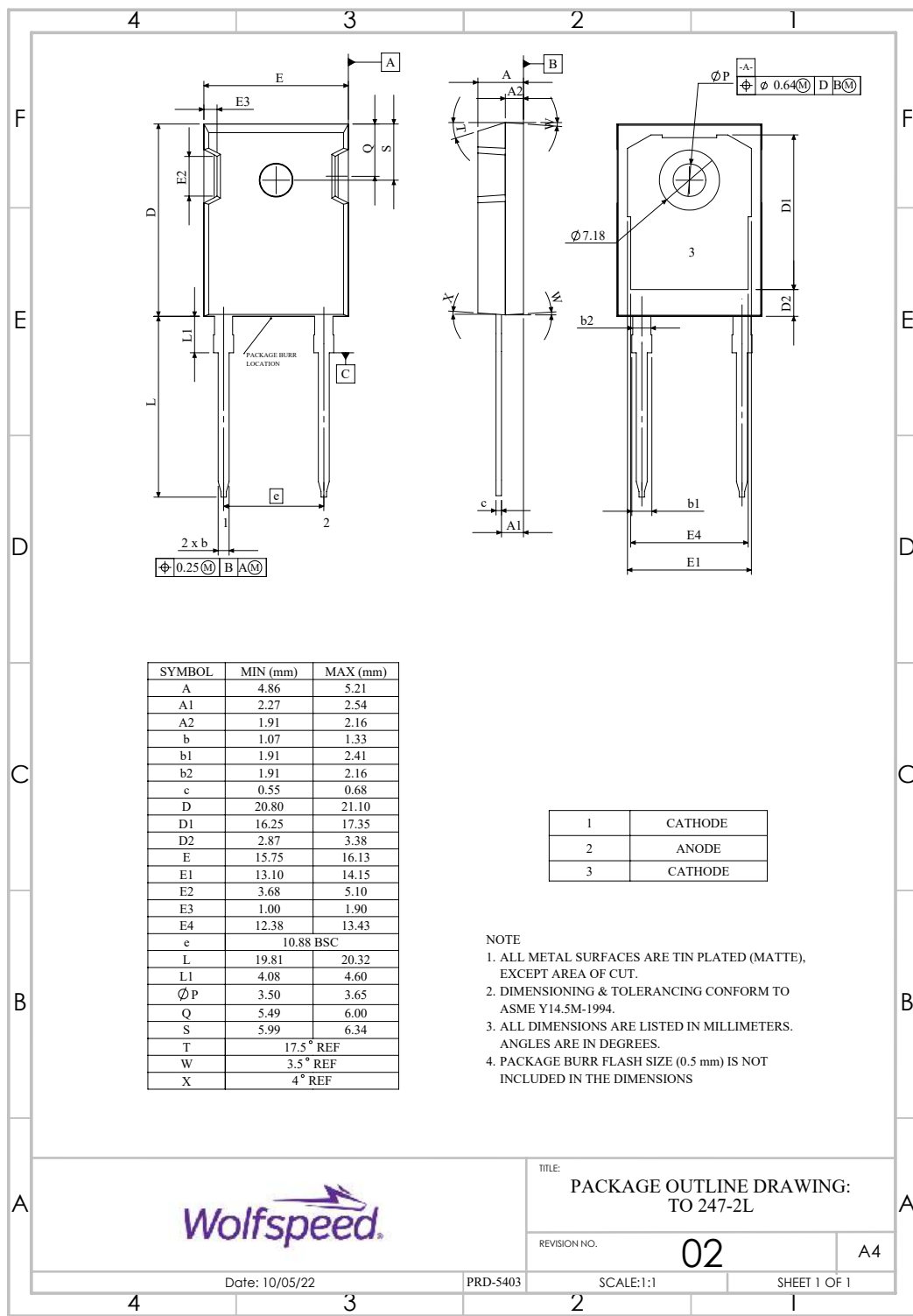


Figure 9
Transient Thermal Impedance



Package Dimensions & Pin-Out

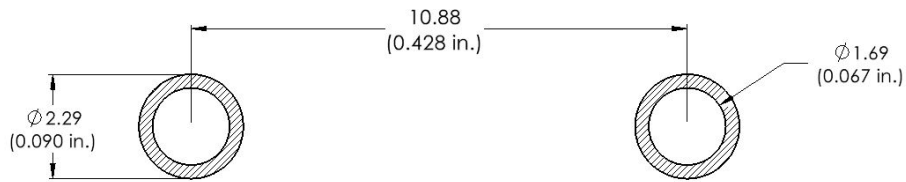
Package: TO-247-2 (All dimensions are in mm)





Recommended Solder Pad Layout

Package: TO-247-2 (All dimensions are in mm)



Product Ordering Information

| Order Number | Packing Type |
|--------------|--------------|
| C6D10170H | Tube |

REACH, RoHS, and Halogen-Free compliance documentation available for this product.



Revision History

| Document Version | Date of Release | Description of changes |
|------------------|-----------------|------------------------|
| 0 | December-2022 | Initial datasheet |



Notes & Disclaimer

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REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact your Wolfspeed representative to ensure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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